

# XN04A88G

Silicon NPN epitaxial planar type (Tr1)

Silicon PNP epitaxial planar type (Tr2)

For low frequency output amplification

**■ Features**

- Two elements incorporated into one package (Tr + Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

**■ Basic Part Number**

- 2SD0601A + UNR211S

**■ Absolute Maximum Ratings**  $T_a = 25^\circ\text{C}$ 

	Parameter	Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	$V_{CBO}$	60	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	50	V
	Emitter-base voltage (Collector open)	$V_{EBO}$	7	V
	Collector current	$I_C$	100	mA
	Peak collector current	$I_{CP}$	200	mA
Tr2	Collector-base voltage (Emitter open)	$V_{CBO}$	-50	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	-50	V
	Collector current	$I_C$	-100	mA
Overall	Total power dissipation	$P_T$	300	mW
	Junction temperature	$T_j$	150	$^\circ\text{C}$
	Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

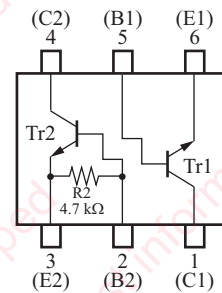
**■ Package**

- Code

Mini6-G3

- Pin Name

1: Collector (Tr1)      4: Collector (Tr2)  
 2: Base (Tr2)      5: Base (Tr1)  
 3: Emitter (Tr2)      6: Emitter (Tr1)

**■ Marking Symbol: 1Z****■ Internal Connection**

XN04A88G

**Panasonic**■ Electrical Characteristics  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$ 

## • Tr1

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{\text{CBO}}$	$I_{\text{C}} = 10\ \mu\text{A}$ , $I_{\text{E}} = 0$	60			V
Collector-emitter voltage (Base open)	$V_{\text{CEO}}$	$I_{\text{C}} = 2\ \text{mA}$ , $I_{\text{B}} = 0$	50			V
Emitter-base voltage (Collector open)	$V_{\text{EBO}}$	$I_{\text{E}} = 10\ \mu\text{A}$ , $I_{\text{C}} = 0$	7			V
Collector-base cutoff current (Emitter open)	$I_{\text{CBO}}$	$V_{\text{CB}} = 20\ \text{V}$ , $I_{\text{E}} = 0$			0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{\text{CEO}}$	$V_{\text{CE}} = 10\ \text{V}$ , $I_{\text{B}} = 0$			100	$\mu\text{A}$
Forward current transfer ratio	$h_{\text{FE}}$	$V_{\text{CE}} = 10\ \text{V}$ , $I_{\text{C}} = 2\ \text{mA}$	160		460	—
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_{\text{C}} = 100\ \text{mA}$ , $I_{\text{B}} = 10\ \text{mA}$		0.1	0.3	V
Collector output capacitance (Common base, input open circuited)	$C_{\text{ob}}$	$V_{\text{CB}} = 10\ \text{V}$ , $I_{\text{E}} = 0$ , $f = 1\ \text{MHz}$		3.5		pF
Transition frequency	$f_{\text{T}}$	$V_{\text{CB}} = 10\ \text{V}$ , $I_{\text{E}} = -2\ \text{mA}$ , $f = 200\ \text{MHz}$		80		MHz

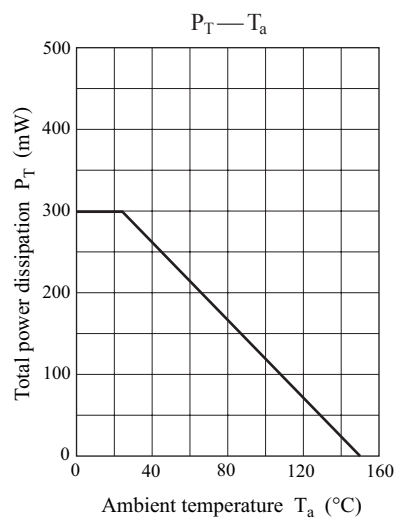
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

## • Tr2

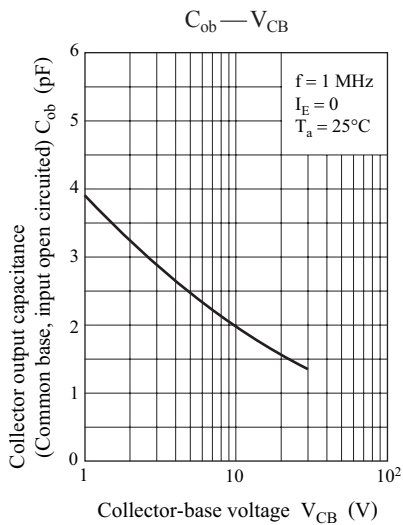
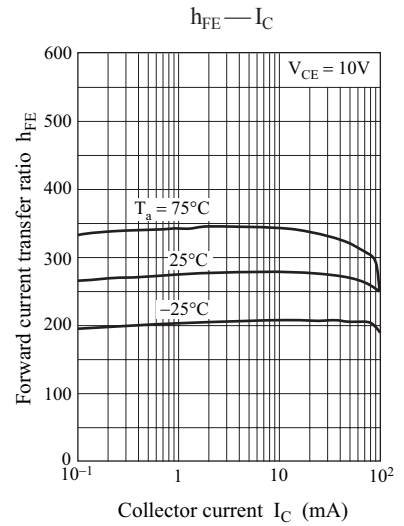
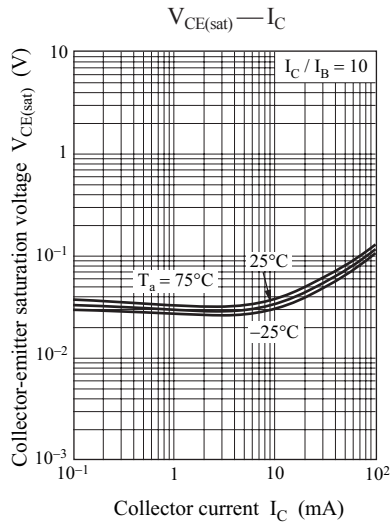
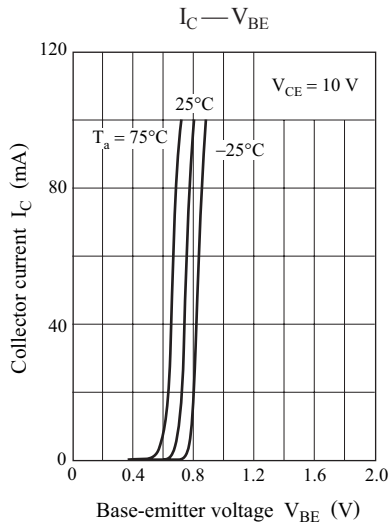
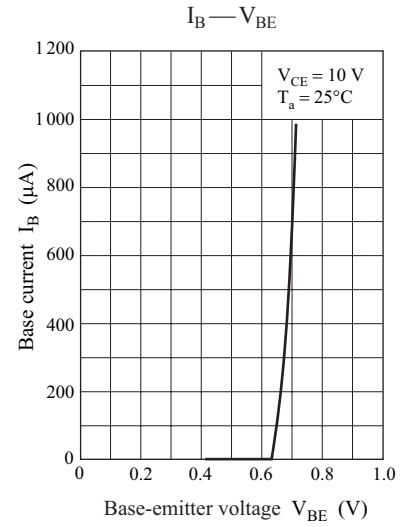
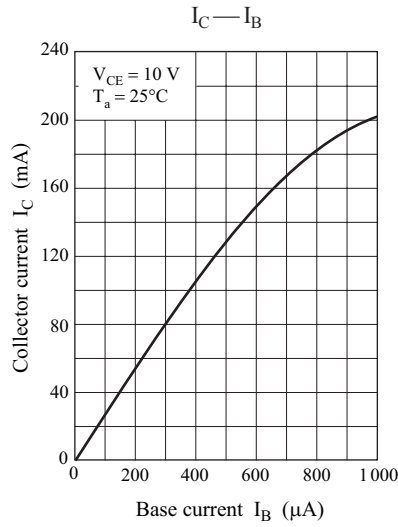
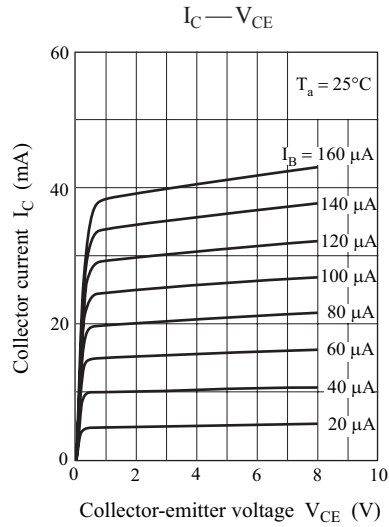
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{\text{CBO}}$	$I_{\text{C}} = -10\ \mu\text{A}$ , $I_{\text{E}} = 0$	-50			V
Collector-emitter voltage (Base open)	$V_{\text{CEO}}$	$I_{\text{C}} = -2\ \text{mA}$ , $I_{\text{B}} = 0$	-50			V
Collector-base cutoff current (Emitter open)	$I_{\text{CBO}}$	$V_{\text{CB}} = -50\ \text{V}$ , $I_{\text{E}} = 0$			-0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{\text{CEO}}$	$V_{\text{CE}} = -50\ \text{V}$ , $I_{\text{B}} = 0$			-0.5	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{\text{EBO}}$	$V_{\text{EB}} = -6\ \text{V}$ , $I_{\text{C}} = 0$			-2.0	mA
Forward current transfer ratio	$h_{\text{FE}}$	$V_{\text{CE}} = -10\ \text{V}$ , $I_{\text{C}} = -5\ \text{mA}$	20			—
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_{\text{C}} = -10\ \text{mA}$ , $I_{\text{B}} = -0.3\ \text{mA}$			-0.25	V
Transition frequency	$f_{\text{T}}$	$V_{\text{CB}} = -10\ \text{V}$ , $I_{\text{E}} = 2\ \text{mA}$ , $f = 200\ \text{MHz}$		100		MHz
Input resistance	$R_2$		-30%	4.7	+30%	k $\Omega$

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

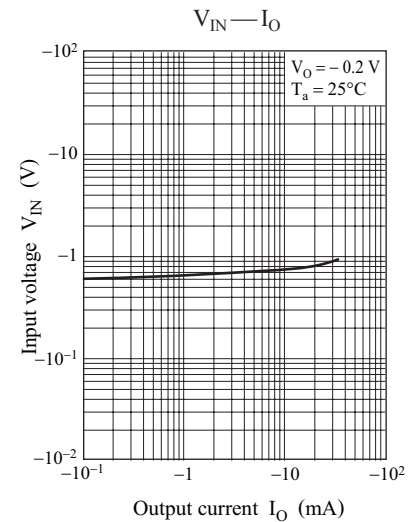
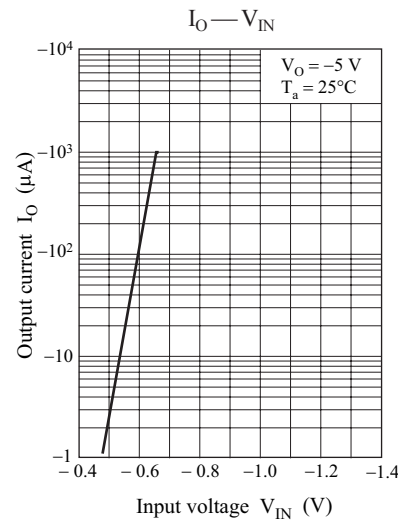
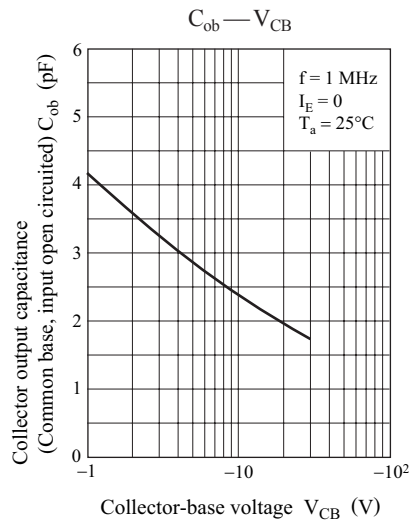
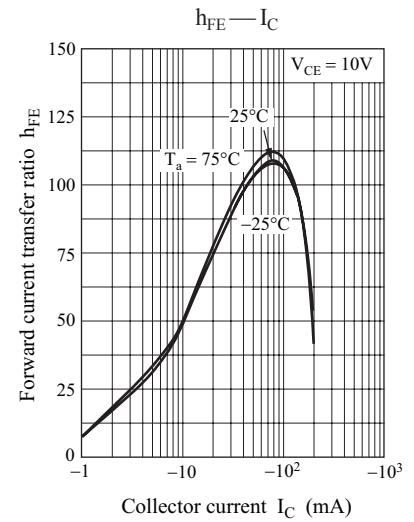
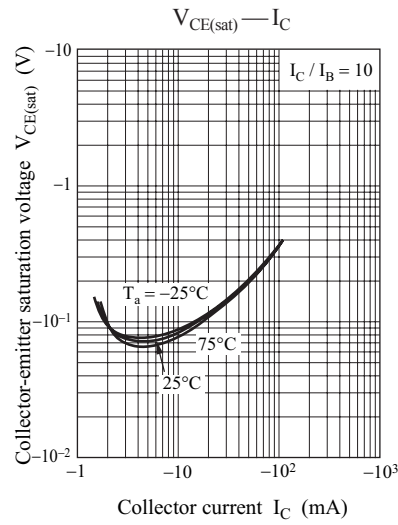
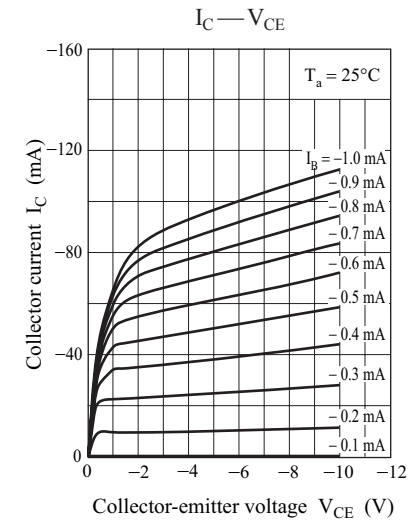
Common characteristics chart



## Characteristics charts of Tr1

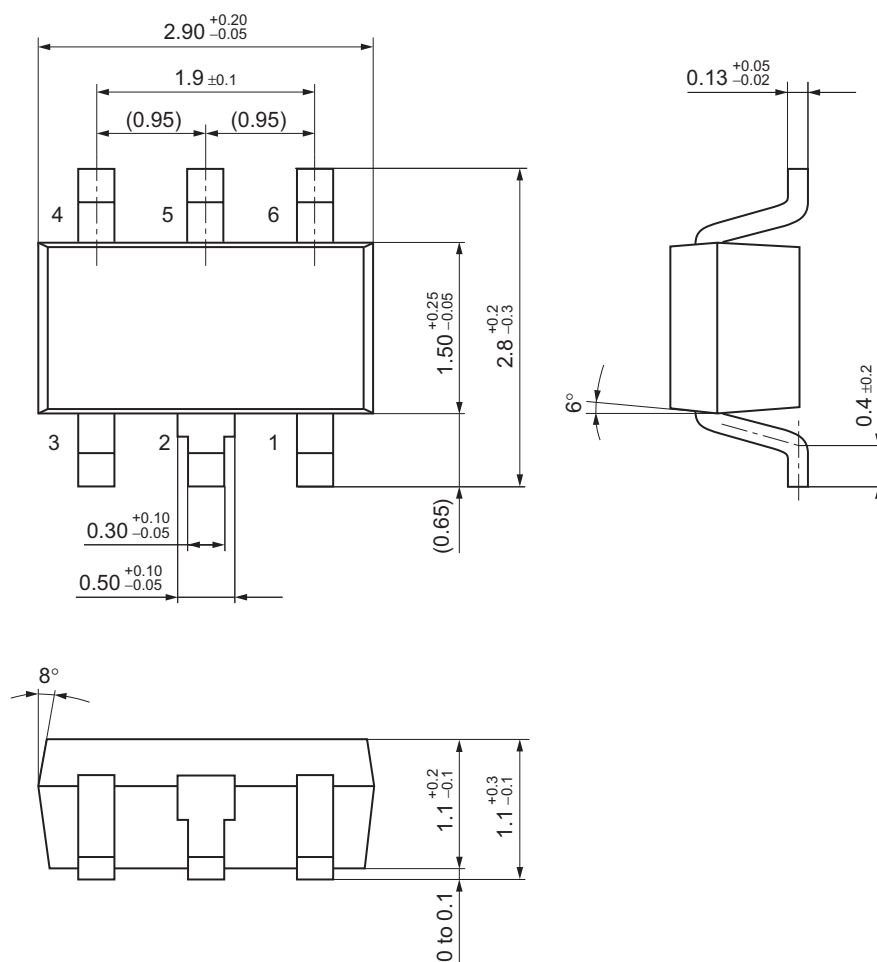


## Characteristics charts of Tr2



## Mini6-G3

Unit: mm



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